P FISMC-01-1020B

SEP 29 2003 SEP 29 2003

September 24, 2003

Commissioner for Patents

P.O.Box 1450

Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572

28 Davis Avenue

Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/613,606 07/03/03

Ying-Lin Chen et al.

A NEW APPROACH TO PREVENT SPACER UNDERCUT BY LOW TEMPERATURE NITRIDATION

Grp. Art Unit:

## INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

## CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on September26, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

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## TSMC-01-1020B

- U.S. Patent 6,200,868 to Mase et al., "Insulated Gate Type Semiconductor Device and Process for Producing the Device," discusses a nitridation process to prevent gate spacer undercut.
- U.S. Patent 6,187,676 to Kim et al., "Integrated Circuit Insulated Electrode Forming Methods Using Metal Silicon Nitride Layers, and Insulated Electrodes so Formed, " discusses a nitridation process to cover an undercut.
- U.S. Patent 6,144,071 to Gardner et al., "Ultrathin Silicon Nitride Containing Sidewall Spacers for Improved Transistor Performance, discloses a transistor provided having a pair of sidewall spacers, each preferably including an ultrathin silicon nitride layer, adjacent to opposed sidewall surfaces of a gate conductor on a semiconductor substrate.
- U.S. Patent 5,939,333 to Hurley et al., "Silicon Nitride Deposition Method," the method in accordance with the present invention is an improved method of forming silicon nitride films to improve the characteristics of semiconductor devices fabricated using silicon nitride films.

Sincerely,

Stephen B. Ackerman,

Reg. No. 37761

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.